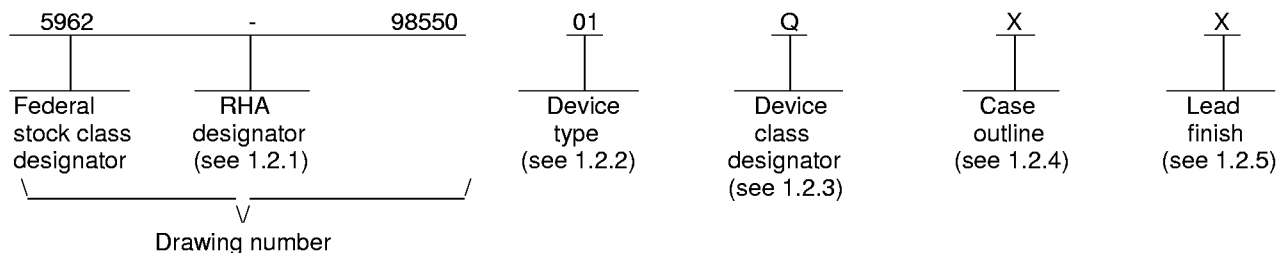


REVISIONS																			
LTR	DESCRIPTION										DATE (YR-MO-DA)					APPROVED			
A	Add device type 02. Modify table I test parameters for device type 01. -lgt										99-05-05					Ray Monnin			
B	Add device type 03. Modify table I test parameters for device type 01. -lgt										99-12-16					Ray Monnin			
REV																			
SHEET																			
REV	B	B	B	B	B														
SHEET	15	16	17	18	19														
REV STATUS OF SHEETS				REV		B	B	B	B	B	B	B	B	B	B	B	B	B	B
				SHEET		1	2	3	4	5	6	7	8	9	10	11	12	13	14
PMIC N/A				PREPARED BY Rajesh Pithadia						DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216									
STANDARD MICROCIRCUIT DRAWING THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS AND AGENCIES OF THE DEPARTMENT OF DEFENSE AMSC N/A				CHECKED BY Rajesh Pithadia															
				APPROVED BY Raymond Monnin															
				DRAWING APPROVAL DATE 99-01-25															
				REVISION LEVEL B															
				SIZE A		CAGE CODE 67268		5962-98550											
				SHEET 1 OF 19															

1. SCOPE

1.1 Scope. This drawing documents two product assurance class levels consisting of high reliability (device classes Q and M) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.

1.2 PIN. The PIN is as shown in the following example:



1.2.1 RHA designator. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. Device class M RHA marked devices meet the MIL-PRF-38535, appendix A specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.

1.2.2 Device type(s). The device type(s) identify the circuit function as follows:

<u>Device type</u>	<u>Generic number</u>	<u>Circuit function</u>
01	LMX2315	1.2 GHz, PLL frequency synthesizer
02	LMX2325	2.5 GHz, PLL frequency synthesizer
03	LMX2305	500 MHz, PLL frequency synthesizer

1.2.3 Device class designator. The device class designator is a single letter identifying the product assurance level as follows:

<u>Device class</u>	<u>Device requirements documentation</u>
M	Vendor self-certification to the requirements for MIL-STD-883 compliant, non-JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A
Q or V	Certification and qualification to MIL-PRF-38535

1.2.4 Case outline(s). The case outline(s) are as designated in MIL-STD-1835 and as follows:

<u>Outline letter</u>	<u>Descriptive designator</u>	<u>Terminals</u>	<u>Package style</u>
X	See figure 1	20	Flat pack

1.2.5 Lead finish. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

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1.3 Absolute maximum ratings. 1/

Power supply voltage:	
V _{CC}	-0.3 V to +6.5 V
V _P	-0.3 V to +6.5 V
Voltage on any pin with GND = 0 V (V _{IN})	
Device types 01 and 02	-0.3 V to +6.5 V
Device type 03	-0.3 V to +0.3 V
Power dissipation (P _D) 2/	1 W
Storage temperature range	-65°C to +150°C
Lead temperature (soldering, 4 seconds)	+260°C
Junction temperature (T _J) 2/	+150°C
Thermal resistance, junction-to-case (θ _{JC}).....	19°C/W
Thermal resistance, junction-to-ambient (θ _{JA}) 2/.....	120°C/W Still air at 0.5 W 86°C/W 500 LF/min air flow at 0.5 W

1.4 Recommended operating conditions.

Power supply voltage:	
V _{CC}	2.7 V to 5.5 V
V _P	V _{CC} to +5.5 V
Ambient operating temperature range (T _A):	
Device type 01	-55°C to +105°C
Device type 02	-55°C to +90°C
Device type 03	-40°C to +105°C

2. APPLICABLE DOCUMENTS

2.1 Government specification, standards, and handbooks. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DoDISS) and supplement thereto, cited in the solicitation.

SPECIFICATION

DEPARTMENT OF DEFENSE

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

STANDARDS

DEPARTMENT OF DEFENSE

- MIL-STD-883 - Test Method Standard Microcircuits.
- MIL-STD-973 - Configuration Management.
- MIL-STD-1835 - Interface Standard For Microcircuit Case Outlines.

HANDBOOKS

DEPARTMENT OF DEFENSE

- MIL-HDBK-103 - List of Standard Microcircuit Drawings (SMD's).
- MIL-HDBK-780 - Standard Microcircuit Drawings.

(Unless otherwise indicated, copies of the specification, standards, and handbooks are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

1/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.
 2/ The maximum power dissipation must be derated at elevated temperatures and is dictated by T_J, θ_{JA}, and T_A. The maximum allowable power dissipation at any temperature is P_D = (T_J - T_A)/θ_{JA} or the number given in 1.3 herein, whichever is lower.

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2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 Item requirements. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein.

3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V or MIL-PRF-38535, appendix A and herein for device class M.

3.2.1 Case outline(s). The case outline(s) shall be in accordance with 1.2.4 herein and figure 1.

3.2.2 Terminal connections. The terminal connections shall be as specified on figure 2.

3.3 Electrical performance characteristics and postirradiation parameter limits. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.

3.4 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are defined in table I.

3.5 Marking. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked as listed in MIL-HDBK-103. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535. Marking for device class M shall be in accordance with MIL-PRF-38535, appendix A.

3.5.1 Certification/compliance mark. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A.

3.6 Certificate of compliance. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein or for device class M, the requirements of MIL-PRF-38535, appendix A and herein.

3.7 Certificate of conformance. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 or for device class M in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.

3.8 Notification of change for device class M. For device class M, notification to DSCC-VA of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-STD-973.

3.9 Verification and review for device class M. For device class M, DSCC, DSCC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

3.10 Microcircuit group assignment for device class M. Device class M devices covered by this drawing shall be in microcircuit group number 119 (see MIL-PRF-38535, appendix A).

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TABLE I. Electrical performance characteristics for device type 01.

Test	Symbol	Conditions 1/ -55°C ≤ T _A ≤ +105°C unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Power supply current	I _{CC}		1, 3	01		8.5	mA
			2			9.5	
Power down current	I _{CC-PWDN}	V _{CC} = 2.7 V	1, 2, 3	01		180	μA
						350	
High level input voltage	V _{IH}	V _{CC} = V _P = 2.7 V 2/ 4/	1, 2, 3	01	0.7 V _{CC}		V
Low level input voltage	V _{IL}	V _{CC} = V _P = 2.7 V 2/ 4/	1, 2, 3	01		0.3 V _{CC}	V
High level input current (clock data)	I _{IH}	V _{IH} = V _{CC} = 5.5 V	1, 2, 3	01	-1.0	1.0	μA
Low level input current (clock data)	I _{IL}	V _{IL} = 0 V	1, 2, 3	01	-1.0	1.0	μA
Oscillator input current	OSC _{IH}	V _{IH} = V _{CC} = 5.5 V	1, 2, 3	01		100	μA
	OSC _{IL}	V _{IL} = 0 V	1, 2, 3	01	-100		μA
High level input current (LE, FC, PWDN)	I _{IH}	V _{IH} = V _{CC} = 5.5 V	1, 2, 3	01	-1.0	1.0	μA
Low level input current (LE, FC, PWDN)	I _{IL}	V _{IL} = 0 V	1, 2, 3	01	-100	1.0	μA
Charge pump tri-state current	I _{DO-TRI}	0.5 V ≤ V _{DO} ≤ 3.1 V, V _{CC} = V _P = 3.6 V	1, 3	01	-2.5	2.5	nA
			2		-25	25	
Charge pump output current	I _{DO-SOURCE}	V _{CC} = V _P = 2.7 V, V _{DO} = 1.35 V	1, 2, 3	01	-3.2		mA
		V _{CC} = V _P = 5.0 V, V _{DO} = 2.5 V			-8.0		
	I _{DO-SINK}	V _{CC} = V _P = 2.7 V, V _{DO} = 1.35 V	1, 2, 3	01		3.2	mA
		V _{CC} = V _P = 5.0 V, V _{DO} = 2.5 V				8.0	

See footnotes at end of table.

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TABLE I. Electrical performance characteristics for device type 01. - Continued.

Test	Symbol	Conditions ^{1/} -55°C ≤ T _A ≤ +105°C unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Charge pump output current magnitude versus voltage	I _{DO} vs V _{DO}	0.5 V ≤ V _{DO} ≤ 4.5 V V _{CC} = V _P = 5.0 V	1, 2, 3	01		15	%
Charge pump output current sink versus source mismatch	I _{DO-SINK} vs I _{DO-SOURCE}	V _{DO} = 2.5 V V _{CC} = V _P = 5.0 V	1, 2, 3	01		10	%
High level output voltage	V _{OH}	I _{OH} = -1.0 mA ^{3/}	1, 2, 3	01	V _{CC} - 0.8		V
	V _{OH(OSCOUT)}	I _{OH} = -200 μA V _{CC} = V _P = 3.0 V			V _{CC} - 0.8		
Low level output voltage	V _{OL}	I _{OL} = 1.0 mA ^{3/}	1, 2, 3	01		0.4	V
	V _{OL(OSCOUT)}	I _{OL} = 200 μA V _{CC} = V _P = 3.0 V				0.4	
Low level open drain output current (PHP)	I _{OL}	V _{OL} = 0.4 V ^{4/}	1, 2, 3	01	1.0		mA
High level open drain output current	I _{OH}	V _{OH} = 5.5 V	1, 2, 3	01		100	μA
Data to clock setup time	t _{CS}	See figure 3 ^{4/} V _{CC} = V _P = 2.7 V	9, 10, 11	01	50		ns
Data to clock hold time	t _{CH}	See figure 3 ^{4/} V _{CC} = V _P = 2.7 V	9, 10, 11	01	10		ns
Clock pulse width high	t _{CWH}	See figure 3 ^{4/} V _{CC} = V _P = 2.7 V	9, 10, 11	01	50		ns
Clock pulse width low	t _{CWL}	See figure 3 ^{4/} V _{CC} = V _P = 2.7 V	9, 10, 11	01	50		ns
Clock to enable setup time	t _{ES}	See figure 3 ^{4/} V _{CC} = V _P = 2.7 V	9, 10, 11	01	50		ns
Enable pulse width	t _{EW}	See figure 3 ^{4/} V _{CC} = V _P = 2.7 V	9, 10, 11	01	50		ns
Maximum operating frequency	f _{IN}	V _{CC} = V _P = 2.7 V ^{4/} Divide Ratio 193, f _{OUT} (Diff) = ±322 Hz	9, 10, 11	01		1.2	GHz
		V _{CC} = V _P = 2.7 V ^{4/} Divide Ratio 385, f _{OUT} (Diff) = ±243 Hz					
Input sensitivity	P _{fIN}	V _{CC} = V _P = 2.7 V ^{4/}	9, 10, 11	01	-15	+5	dBm
		V _{CC} = 5.5 V ^{4/}	9, 10		-9	6	
			11		-7	6	

See footnotes at end of table.

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TABLE I. Electrical performance characteristics for device type 02.

Test	Symbol	Conditions ^{1/} -55°C ≤ T _A ≤ +90°C unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Power supply current	I _{CC}	V _{CC} = 5.5 V	1, 2, 3	02		15	mA
Power down current	I _{CC-PWDN}	V _{CC} = 2.7 V	1, 2, 3	02		180	μA
		V _{CC} = 5.5 V				350	
High level input voltage	V _{IH}	V _{CC} = V _P = 2.7 V <u>2/ 4/</u>	1, 2, 3	02	0.7 V _{CC}		V
Low level input voltage	V _{IL}	V _{CC} = V _P = 2.7 V <u>2/ 4/</u>	1, 2, 3	02		0.3 V _{CC}	V
High level input current (clock data)	I _{IH}	V _{IH} = V _{CC} = 5.5 V	1, 2, 3	02	-1.0	1.0	μA
Low level input current (clock data)	I _{IL}	V _{IL} = 0 V, V _{CC} = 5.5 V	1, 2, 3	02	-1.0	1.0	μA
Oscillator input current	OSC _{IH}	V _{IH} = V _{CC} = 5.5 V	1, 2, 3	02		100	μA
	OSC _{IL}	V _{IL} = 0 V, V _{CC} = 5.5 V	1, 2, 3	02	-100		
High level input current (LE, FC, PWDN)	I _{IH}	V _{IH} = V _{CC} = 5.5 V	1, 2, 3	02	-1.0	1.0	μA
Low level input current (LE, FC, PWDN)	I _{IL}	V _{IL} = 0 V, V _{CC} = 5.5 V	1, 2, 3	02	-100	1.0	μA
Charge pump tri-state current	I _{DO-TRI}	0.5 V ≤ V _{DO} ≤ 3.1 V V _{CC} = V _P = 3.6 V	1, 3	02	-2.5	2.5	nA
			2		-20	20	
Charge pump output current	I _{DO-SOURCE}	V _{CC} = V _P = 2.7 V, V _{DO} = 1.35 V	1, 3	02	-3.0		mA
			2		-3.2		
		V _{CC} = V _P = 5.0 V, V _{DO} = 2.5 V	1, 3	02	-8.0		mA
			2		-8.2		

See footnotes at end of table.

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TABLE I. Electrical performance characteristics for device type 02. - Continued.

Test	Symbol	Conditions ^{1/} -55°C ≤ T _A ≤ +90°C unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Charge pump output current	I _{DO-SINK}	V _{CC} = V _P = 2.7 V, V _{DO} = 1.35 V	1, 3	02		3.0	mA
			2			3.2	
		V _{CC} = V _P = 5.0 V, V _{DO} = 2.5 V	1, 3	02		8.0	mA
			2			8.2	
Charge pump output current magnitude variation versus voltage	I _{DO} vs V _{DO}	V _{CC} = V _P = 5.0 V, 0.5 V ≤ V _{DO} ≤ 4.5 V	1, 2, 3	02		15	%
Charge pump output current sink versus source mismatch	I _{DO-SINK} vs I _{DO-SOURCE}	V _{CC} = V _P = 5.0 V, V _{DO} = 2.5 V	1, 2, 3	02		10	%
High level output voltage	V _{OH}	I _{OH} = -1.0 mA ^{3/} V _{CC} = V _P = 2.7 V	1, 2, 3	02	V _{CC} -0.8		V
	V _{OH(OSCOUT)}	I _{OH} = -200 μA			V _{CC} -0.8		
Low level output voltage	V _{OL}	I _{OL} = 1.0 mA ^{3/} V _{CC} = V _P = 2.7 V	1, 2, 3	02		0.4	V
	V _{OL(OSCOUT)}	I _{OL} = 200 μA				0.4	
Low level open drain output current (PHP)	I _{OL}	V _{CC} = V _P = 5.5 V ^{4/} V _{OL} = 0.4 V	1, 2, 3	02	1.0		mA
High level open drain output current (PHP)	I _{OH}	V _{CC} = V _P = 5.5 V V _{OL} = 5.5 V	1, 2, 3	02		100	μA
Data to clock setup time	t _{CS}	See Data Input Timing for figure 3 V _{CC} = V _P = 2.7 V ^{4/}	9, 10, 11	02	50		ns
Data to clock hold time	t _{CH}	See Data Input Timing for figure 3 V _{CC} = V _P = 2.7 V ^{4/}	9, 10, 11	02	10		ns
Clock pulse width high	t _{CWH}	See Data Input Timing for figure 3 V _{CC} = V _P = 2.7 V ^{4/}	9, 10, 11	02	50		ns
Clock pulse width low	t _{CWL}	See Data Input Timing for figure 3 V _{CC} = V _P = 2.7 V ^{4/}	9, 10, 11	02	50		ns
Clock to enable setup time	t _{ES}	See Data Input Timing for figure 3 V _{CC} = V _P = 2.7 V ^{4/}	9, 10, 11	02	50		ns

See footnotes at end of table.

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TABLE I. Electrical performance characteristics for device type 02. - Continued.

Test	Symbol	Conditions <u>1/</u> -55°C ≤ T _A ≤ +90°C unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Enable pulse width	t _{EW}	See Data Input Timing for figure 3 V _{CC} = V _P = 2.7 V <u>4/</u>	9, 10, 11	02	50		ns
Maximum operating frequency	f _{IN}	V _{CC} = V _P = 2.7 V <u>4/</u>	9, 11	02		2.5	GHz
			10			2.2	
Input sensitivity	P _{fIN}	V _{CC} = V _P = 2.7 V, <u>4/</u> F _{IN} = 2.5 GHz	9, 11	02	-10	+5	dBm
		V _{CC} = V _P = 2.7 V, <u>4/</u> F _{IN} = 2.2 GHz	10		-10	+1	
		V _{CC} = V _P = 5.5 V, <u>4/</u> F _{IN} = 2.5 GHz	9, 11		-5	+6	
		V _{CC} = V _P = 5.5 V, <u>4/</u> F _{IN} = 2.2 GHz	10		-5	+2	

See footnotes at end of table.

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TABLE I. Electrical performance characteristics for device type 03.

Test	Symbol	Conditions 1/ -40°C ≤ T _A ≤ +105°C unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Power supply current	I _{CC}	V _{CC} = 5.5 V	1, 2, 3	03		6	mA
Power down current	I _{CC-PWDN}	V _{CC} = 2.7 V	1, 2, 3	03		180	μA
		V _{CC} = 5.5 V				400	
High level input voltage	V _{IH}	V _{CC} = V _P = 2.7 V 2/ 4/	1, 2, 3	03	0.7 V _{CC}		V
Low level input voltage	V _{IL}	V _{CC} = V _P = 2.7 V 2/ 4/	1, 2, 3	03		0.3 V _{CC}	V
High level input current (clock data)	I _{IH}	V _{IH} = V _{CC} = 5.5 V	1, 2, 3	03	-1.0	1.0	μA
Low level input current (clock data)	I _{IL}	V _{IL} = 0 V, V _{CC} = 5.5 V	1, 2, 3	03	-1.0	1.0	μA
Oscillator input current	OSC _{IH}	V _{IH} = V _{CC} = 5.5 V	1, 2, 3	03		100	μA
	OSC _{IL}	V _{IL} = 0 V, V _{CC} = 5.5 V	1, 2, 3	03	-100		μA
High level input current (LE, FC, PWDN)	I _{IH}	V _{IH} = V _{CC} = 5.5 V	1, 2, 3	03	-1.0	1.0	μA
Low level input current (LE, FC, PWDN)	I _{IL}	V _{IL} = 0 V, V _{CC} = 5.5 V	1, 2, 3	03	-100	1.0	μA
Charge pump tri-state current	I _{DO-TRI}	0.5 V ≤ V _{DO} ≤ 3.1 V V _{CC} = V _P = 3.6 V	1, 3	03	-2.5	2.5	nA
			2		-25	25	
Charge pump output current	I _{DO-SOURCE}	V _{CC} = V _P = 2.7 V, V _{DO} = 1.35 V	1, 2, 3	03	-3.0		mA
		V _{CC} = V _P = 5.0 V, V _{DO} = 2.5 V	1, 2, 3	03	-8.0		mA

See footnotes at end of table.

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TABLE I. Electrical performance characteristics for device type 03. - Continued.

Test	Symbol	Conditions ^{1/} -40°C ≤ T _A ≤ +105°C unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Charge pump output current	I _{DO-SINK}	V _{CC} = V _P = 2.7 V, V _{DO} = 1.35 V	1, 2, 3	03		3.0	mA
		V _{CC} = V _P = 5.0 V, V _{DO} = 2.5 V	1, 2, 3	03		8.0	mA
Charge pump output current magnitude variation versus voltage	I _{DO} vs V _{DO}	V _{CC} = V _P = 5.0 V, 0.5 V ≤ V _{DO} ≤ 4.5 V	1, 2, 3	03		15	%
Charge pump output current sink versus source mismatch	I _{DO-SINK} vs I _{DO-SOURCE}	V _{CC} = V _P = 5.0 V, V _{DO} = 2.5 V	1, 2, 3	03		10	%
High level output voltage	V _{OH}	I _{OH} = -1.0 mA ^{3/}	1, 2, 3	03	V _{CC}		V
	V _{OH(OSCOUT)}	I _{OH} = -200 μA V _{CC} = V _P = 3.0 V			-0.8		
Low level output voltage	V _{OL}	I _{OL} = 1.0 mA ^{3/}	1, 2, 3	03		0.4	V
	V _{OL(OSCOUT)}	I _{OL} = 200 μA V _{CC} = V _P = 3.0 V				0.4	
Low level open drain output current (PHP)	I _{OL}	V _{CC} = V _P = 5.5 V ^{4/} V _{OL} = 0.4 V	1, 2, 3	03	1.0		mA
High level open drain output current (PHP)	I _{OH}	V _{CC} = V _P = 5.5 V V _{OL} = 5.5 V	1, 2, 3	03		100	μA
Data to clock setup time	t _{CS}	See Data Input Timing for figure 3 V _{CC} = V _P = 2.7 V ^{4/}	9, 10, 11	03	50		ns
Data to clock hold time	t _{CH}	See Data Input Timing for figure 3 V _{CC} = V _P = 2.7 V ^{4/}	9, 10, 11	03	10		ns
Clock pulse width high	t _{CWH}	See Data Input Timing for figure 3 V _{CC} = V _P = 2.7 V ^{4/}	9, 10, 11	03	50		ns
Clock pulse width low	t _{CWL}	See Data Input Timing for figure 3 V _{CC} = V _P = 2.7 V ^{4/}	9, 10, 11	03	50		ns
Clock to enable setup time	t _{ES}	See Data Input Timing for figure 3 V _{CC} = V _P = 2.7 V ^{4/}	9, 10, 11	03	50		ns

See footnotes at end of table.

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TABLE I. Electrical performance characteristics for device type 03. - Continued.

Test	Symbol	Conditions ^{1/} -40°C ≤ T _A ≤ +105°C unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Enable pulse width	t _{EW}	See Data Input Timing for figure 3 V _{CC} = V _P = 2.7 V ^{4/}	9, 10, 11	03	50		ns
Maximum operating frequency	f _{IN}	V _{CC} = V _P = 2.7 V ^{4/}	9	03		500	MHz
			10, 11			450	
Input sensitivity	P _{fIN}	V _{CC} = V _P = 2.7 V, ^{4/} F _{IN} = 500 MHz	9	03	-10	+1	dBm
		V _{CC} = V _P = 2.7 V, ^{4/} F _{IN} = 450 MHz	10, 11		-10	+1	
		V _{CC} = V _P = 5.5 V, ^{4/} F _{IN} = 500 MHz	9		-7	+3	
		V _{CC} = V _P = 5.5 V, ^{4/} F _{IN} = 450 MHz	10, 11		-5	+2	

^{1/} Unless otherwise specified, device type 01 V_{CC} = 5.5 V and V_P = 5.5 V, -55°C ≤ T_A ≤ +105°C; device type 02 V_{CC} = 3.0 V and V_P = 3.0 V, -55°C ≤ T_A ≤ +90°C, device type 03 V_{CC} = 5.5 V and V_P = 5.5 V, -40°C ≤ T_A ≤ +105°C.

^{2/} Except f_{IN} and OSCIN.

^{3/} Except OSCOUT.

^{4/} Parameters not directly tested, but used as setup conditions.

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4. QUALITY ASSURANCE PROVISIONS

4.1 Sampling and inspection. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.

4.2 Screening. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection.

4.2.1 Additional criteria for device class M.

a. Burn-in test, method 1015 of MIL-STD-883.

(1) Test condition A, B, C or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.

(2) $T_A = +125 \cdot C$, minimum.

b. Interim and final electrical test parameters shall be as specified in table II herein.

4.2.2 Additional criteria for device classes Q and V.

a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.

b. Interim and final electrical test parameters shall be as specified in table II herein.

c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.

4.3 Qualification inspection for device classes Q and V. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4 Conformance inspection. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified herein except where option 2 of MIL-PRF-38535 permits alternate in-line control testing. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

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Case X

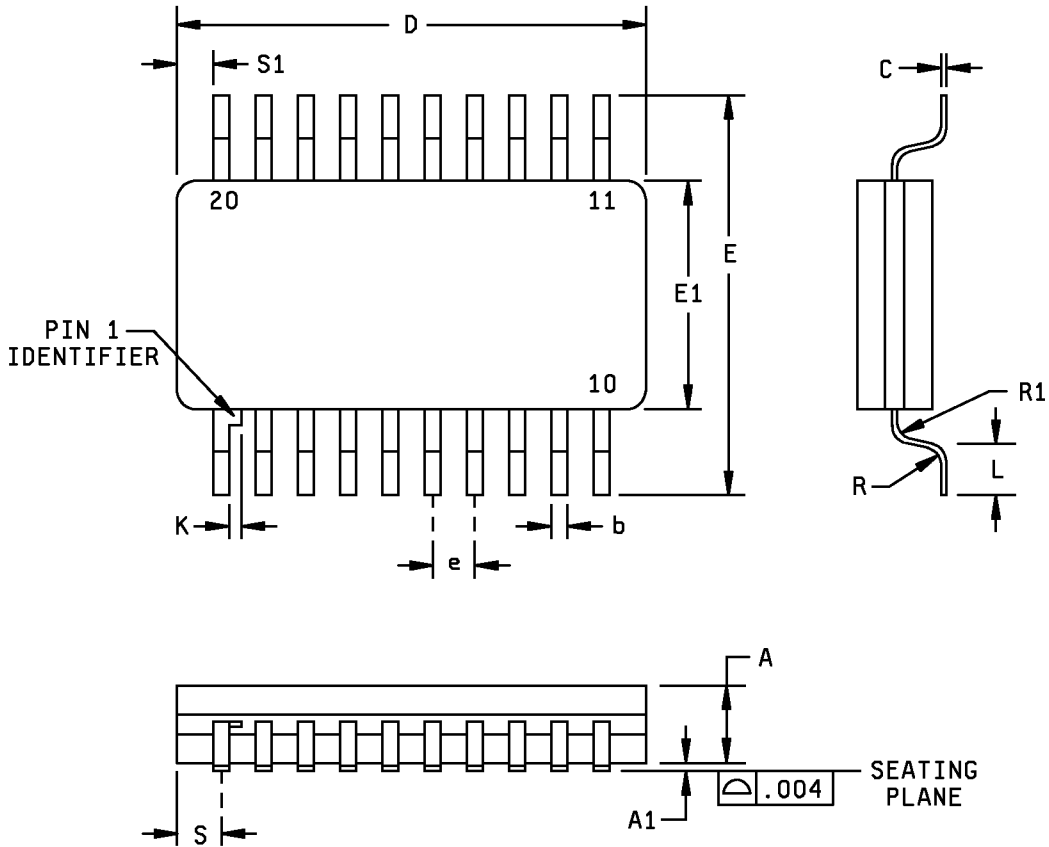


FIGURE 1. Case outline.

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Case X

Ltr	Inches		Millimeters		Notes
	Min	Max	Min	Max	
A	.060	.090	1.53	2.29	
A1	.004	.012	0.10	0.30	
b	.015	.019	0.38	0.48	2
C	.004	.008	0.10	0.20	2
D	----	.540	----	13.72	
E	.400	.420	10.16	10.67	
E1	.260	.270	6.61	6.86	
e	.045	.055	1.15	1.39	
K	.008	.012	0.20	0.30	
L	.037	.043	0.94	1.09	
R	.015 BSC		0.38 BSC		
R1	.015 BSC		0.38 BSC		
S	----	.045	----	1.14	
S1	.005	----	0.13	----	

NOTES:

1. The US government preferred system of measurement is the metric SI system. However, since this item was originally designed using inch-pound units of measurement, in the event of conflict between the metric and inch-pound units, the inch-pound units shall take precedence.
2. Maximum limit may be increased by .003 inches after lead finish is applied.

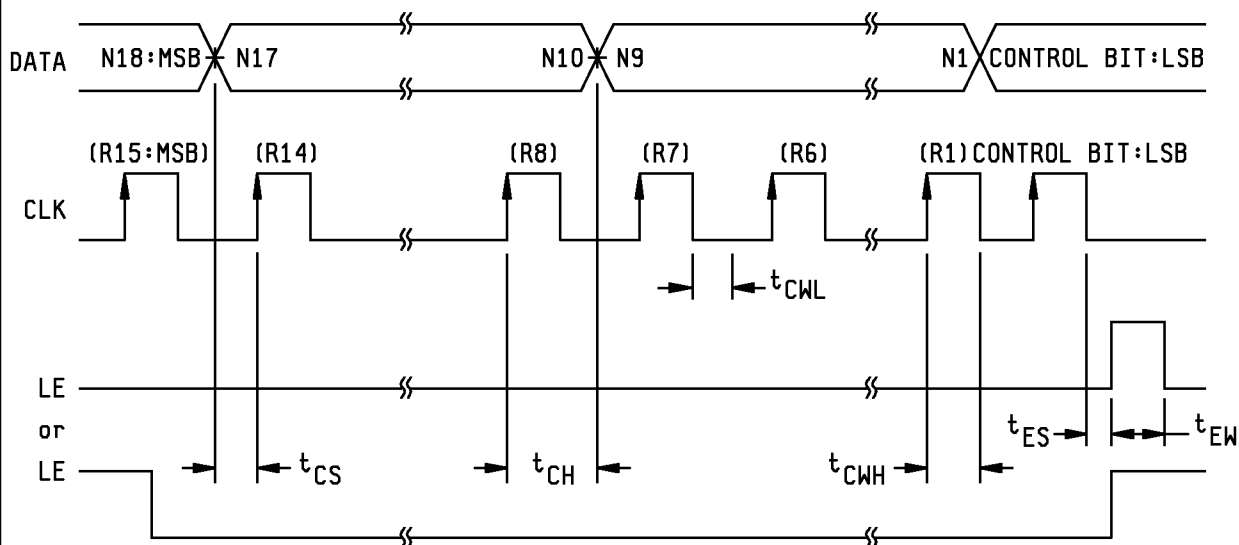
FIGURE 1. Case outline - Continued.

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Device type	All
Case outline	X
Terminal number	Terminal symbol
1	OSCIN
2	NC
3	OSCOU
4	V _P
5	V _{CC}
6	D _O
7	GND
8	LD
9	NC
10	F _{IN}
11	CLOCK
12	NC
13	DATA
14	LE
15	FC
16	BISW
17	F _{OUT}
18	φ _P
19	PWDN
20	φ _R

FIGURE 2. Terminal connections.

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NOTES:

1. Data in parenthesis indicates programmable reference divider data.
2. Data shifted into register in clock rising edges.
3. Data is shifted in MSB first.

FIGURE 3. Timing diagram.

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TABLE II. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)	Subgroups (in accordance with MIL-PRF-38535, table III)	
	Device class M	Device class Q	Device class V
Interim electrical Parameters (see 4.2)	1	1	1
Final electrical Parameters (see 4.2)	1, 2, 3, 9, 10, 11 <u>1/</u>	1, 2, 3, 9, 10, 11 <u>1/</u>	1, 2, 3, 9, 10, 11 <u>1/</u>
Group A test Requirements (see 4.4)	1, 2, 3, 9, 10, 11	1, 2, 3, 9, 10, 11	1, 2, 3, 9, 10, 11
Group C end-point electrical Parameters (see 4.4)	1, 2, 3	1, 2, 3	1, 2, 3
Group D end-point electrical Parameters (see 4.4)	1, 2, 3	1, 2, 3	1, 2, 3
Group E end-point electrical Parameters (see 4.4)	----	----	----

1/ PDA applies to subgroup 1.

4.4.1 Group A inspection.

- a. Tests shall be as specified in table II herein.
- b. Subgroups 4, 5, 6, 7, and 8 in table I, method 5005 of MIL-STD-883 shall be omitted.

4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table II herein.

4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:

- a. Test condition A, B, C or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
- b. $T_A = +125 \cdot C$, minimum.
- c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.

4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table II herein.

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4.4.4 Group E inspection. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).

- a. End-point electrical parameters shall be as specified in table II herein.
- b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535, appendix A for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at $T_A = +25^{\circ}\text{C} \pm 5^{\circ}\text{C}$, after exposure, to the subgroups specified in table II herein.
- c. When specified in the purchase order or contract, a copy of the RHA delta limits shall be supplied.

5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

6. NOTES

6.1 Intended use. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.1.1 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor prepared specification or drawing.

6.1.2 Substitutability. Device class Q devices will replace device class M devices.

6.2 Configuration control of SMD's. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-973 using DD Form 1692, Engineering Change Proposal.

6.3 Record of users. Military and industrial users should inform Defense Supply Center Columbus when a system application requires configuration control and which SMD's are applicable to that system. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0525.

6.4 Comments. Comments on this drawing should be directed to DSCC-VA, Columbus, Ohio 43216-5000, or telephone (614) 692-0674.

6.5 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

6.6 Sources of supply.

6.6.1 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DSCC-VA and have agreed to this drawing.

6.6.2 Approved sources of supply for device class M. Approved sources of supply for class M are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DSCC-VA.

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STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 99-12-16

Approved sources of supply for SMD 5962-98550 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DSCC-VA. This bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535.

Standard microcircuit drawing PIN <u>1/</u>	Vendor CAGE number	Vendor similar PIN <u>2/</u>
5962-9855001QXA	27014	LMX2315WG-QML
5962-9855002QXA	27014	LMX2325WG-QML
5962-9855003QXA	27014	LMX2305WG-QML

1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.

2/ **Caution.** Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGE number

27014

Vendor name and address

National Semiconductor
2900 Semiconductor Drive
P.O. Box 58090
Santa Clara, CA 95052-8090

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in the information bulletin.